

ABSTRACT OF THE DISCLOSURE

There is provided a bipolar transistor that enables a desirably enhanced high-frequency performance to be obtained when used as an oscillation amplifier of an oscillation circuit, and that is miniaturized and reduced in cost. A capacitance adjustment line (11) connected to a base pad (7) forms a parasitic capacitor with respect to an N⁺ collector substrate by interposing an insulating film (3) and an N collector substrate therebetween, thereby increasing collector-base capacitance C_{cb}. This capacitor is incorporated into a bipolar transistor, which functions as an oscillation amplifier and has a small transistor operation region (2), at least as a part of a balance capacitor constituting the oscillation circuit in the course of production of a semiconductor.